



## **NPN RF Amplifier**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

#### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.0	V
I <sub>C</sub>	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

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1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		PN3563	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction to Ambient	357	°C/W

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# NPN RF Amplifier (continued)

V <sub>(BR)CBO</sub> Coll V <sub>(BR)EBO</sub> Emi	TERISTICS ector-Emitter Sustaining Voltage* ector-Base Breakdown Voltage tter-Base Breakdown Voltage ector Cutoff Current	$I_{C} = 3.0 \text{ mA}, I_{B} = 0$ $I_{C} = 100 \ \mu\text{A}, I_{E} = 0$ $I_{E} = 10 \ \mu\text{A}, I_{C} = 0$	15 30	Γ	
V <sub>CEO(SUS)</sub> Coll V <sub>(BR)CBO</sub> Coll V <sub>(BR)EBO</sub> Emi	ector-Emitter Sustaining Voltage* ector-Base Breakdown Voltage tter-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$			
V <sub>(BR)CBO</sub> Coll V <sub>(BR)EBO</sub> Emi	ector-Base Breakdown Voltage tter-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{E} = 0$			V
V <sub>(BR)EBO</sub> Emi	tter-Base Breakdown Voltage	· ·			V
	ector Cutoff Current		2.0		V
		$V_{CB} = 15 \text{ V}, I_E = 0$ $V_{CB} = 15 \text{ V}, T_A = 150^{\circ}\text{C}$		0.05 5.0	μA nA
ON CHARACT	ERISTICS*				
	Current Gain	I <sub>C</sub> = 8.0 mA, V <sub>CE</sub> = 10 V	20	200	
	L CHARACTERISTICS	I <sub>C</sub> = 8.0 mA, V <sub>CE</sub> = 10 V,	600	1500	MHz
		f = 100 MHz			
C <sub>obo</sub> Out	put Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ $V_{CB} = 0, I_E = 0, f = 1.0 \text{ MHz}$		1.7 3.0	pF pF
C <sub>ibo</sub> Inp	ut Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0, f = 140 \text{ MHz}$		2.0	pF
	all-Signal Current Gain	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 MHz	20	250	
rb'C <sub>C</sub> Col	lector Base Time Constant	$I_{C} = 8.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 79.8 MHz	8.0	25	pS
FUNCTIONAL	TEST				
	blifier Power Gain	$I_{C} = 8.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 200 MHz	14	26	dB
*Pulse Test: Pulse Widt	h≤300 μs, Duty Cycle≤2.0%				

PN3563



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